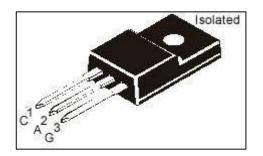
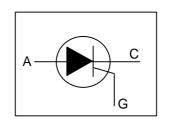




An IS/ISO 9002 and IECQ Certified Manufacturer

THYRISTORS BT151X





TO-220FP Fully Isolated Plastic Package

For use in Applications Requiring High Bidirectional Blocking Voltage Capability and high Thermal Cycling Performance. Typical Applications include Motor Control, Industrial and Domestic Lighting, Heating and Static Switching.

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITION	VALUE		UNIT
		BT151X-	500	650	
Repetitive Peak Off State Voltage	V_{DRM} , V_{RRM}		*500	*650	V
Average On State Current	I _{T (AV)}	half sine wave, T _{hs} ≤ 87°C	5.7		Α
RMS On State Current	I _{T (RMS)}	all conduction angles	9.0		Α
Non Repetitive Peak On State Current	1 .	half sine wave, T _J =25°C			
Non Repetitive Feak On State Current	I _{TSM}	prior to surge			
		t=10ms	100		Α
		t=8.3ms	110		Α
I ² t for Fusing	l ² t	t=10ms	50		A^2s
Repetitive Rate Of Rise of On State	dl _⊤ /dt	I_{TM} =20A, I_{G} =50mA,	50		A/μs
Current After Triggering	di y /di	dl _G /dt=50mA/μs			
Peak Gate Current	I _{GM}		2.0		Α
Peak Gate Voltage	V_{GM}		5.	0	V
Peak Reverse Gate Voltage	V_{RGM}		5.0		V
Peak Gate Power	P_{GM}		5.0		W
Average Gate Power	P _{G (AV)}	Over any 20ms period	0.5		W
Storage Temperature	T _{stg}		- 40 to +150		°C
Operating Junction Temperature	T _j		125		°C

ISOLATION LIMITING VALUE and CHARACTERISTIC (T_{hs}=25°C unless specified otherwise)

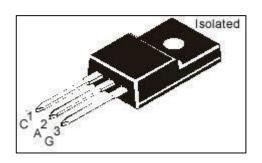
100 EATION Eliminated TALOE and OTIANAOTENIOTIO (This-20 of anicos openiou outletwise)						
PARAMETER	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
R.M.S Isolation Voltage from all three		f=50-60 Hz; sinusoidal waveform; R.H. < 65%;			2500	
_	V_{ISOL}					V
terminals to external heatsink		clean and dustfree				
Capacitance from T2 to external heatsink	C _{ISOL}	f=1MHz		10		pF
				1		

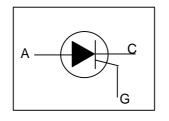
THERMAL RESISTANCE

Junction to Heatsink	R _{th (j-hs)}	with heatsink compound	4.5 max	K/W
		without heatsink compound	6.5 max	K/W
Junction to Ambient	R _{th (j-a)}	in free air	55 typ	K/W

^{*}Although not recommended, off state voltage upto 800V may be applied without damage, but the thyristor may switch to the on state. The rate of rise of current should not exceed 15A/ms

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ELECTRICAL CHARACTERISTICS (T_J=25°C unless specified otherwise)

DADAMETED	BAAV	LINIT				
PARAMETER	SYMBOL	TEST CONDITION	MIN	MAX	UNIT	
Gate Trigger Current	I _{GT}	$V_{D}=12V, I_{T}=0.1A$		15	mA	
Latching Current	ار	$V_{D}=12V, I_{GT}=0.1A$		40	mΑ	
Holding Current	I _H	$V_{D}=12V, I_{GT}=0.1A$		20	mΑ	
On State Voltage	V_{T}	I _T =23A		1.75	V	
Gate Trigger Voltage	V_{GT}	$V_D = 12V, I_T = 0.1A$		1.5	V	
		$V_D=V_{DRM}$ (max), $I_T=0.1A, T_J=125$ °C	0.25		V	
Off State Leakage Current	I _{D,} I _R	$V_D = V_{DRM}$ (max), $V_R = V_{RRM}$ (max) $T_J = 125$ °C		0.5	mA	

DYNAMIC CHARACTERISTICS

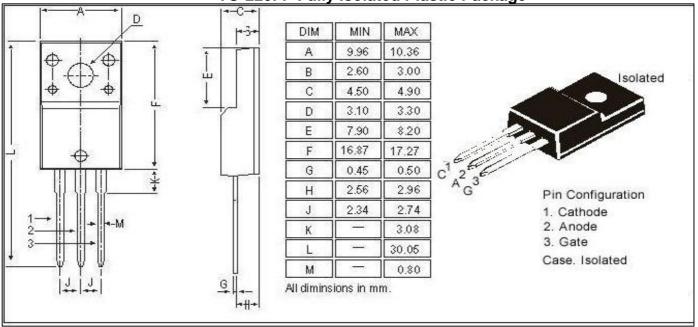
PARAMETER	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Critical Rate of Rise of Off State Voltage	$\begin{array}{c} V_{DM}\text{=}67\%\ V_{DRM}\text{=}max, \\ \text{dV}_{D}\text{/}\text{dt} & T_{J}\text{=}125^{\circ}\text{C, exponential} \\ & \text{waveform} \end{array}$					
		gate open circuit	50			V/μs
		$R_{GK} = 100\Omega$	200			V/μs
Gate Controlled Turn On time	t _{gt}	I_{TM} =40A, V_D = V_{DRM} (max), I_G =0.1A, dI_G / dt =5A/ μ s		2.0		μs
Circuit Commutated Turn Off time	t _q	V_{DM} =67% V_{DRM} =(max), T_J =125°C, I_{TM} =20A, V_R =25V, dI_{TM} /dt=30A/ μ s, dV_D /dt=50V/ μ s, R_{GK} =100 Ω		70		μs

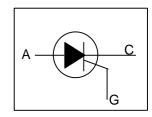
Marking	BT151X-500	BT151X-650
	CDXX	CDXX
	BT151X	BT151X
	- 500	- 650
XX=Date Code		

BT151XRev020103E

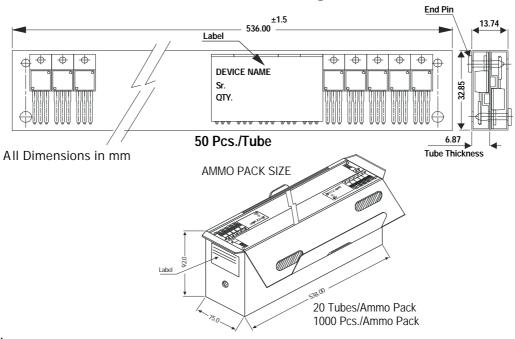
TO-220FP Fully Isolated Plastic Package







TO-220 Tube Packing



Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details Net Weight / Oty		Size	Qty	Size	Qty	Gr Wt
TO-220 /FP	200 pcs/polybag	396 gm/200 pcs	3" x 7.5" x 7.5"	1.0K	17" x 15" x 13.5"	16.0K	36 kgs
	50 pcs/tube	120 gm/50 pcs	3.5" x 3.7" x 21.5"	1.OK	19" x 19" x 19"	10.0K	29 kgs

Notes BT151X

TO-220FP Fully Isolated Plastic Package

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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